



SPN8878 N-Channel Enhancement Mode MOSFET

DESCRIPTION

The SPN8878 is the N-Channel logic enhancement mode power field effect transistors are produced using high cell density , DMOS trench technology. The SPN8878 has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers. It has been optimized for low gate charge, low $R_{DS(ON)}$ and fast switching speed.

FEATURES

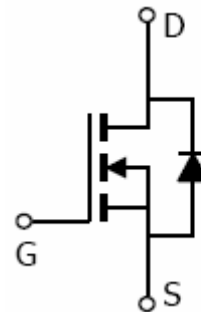
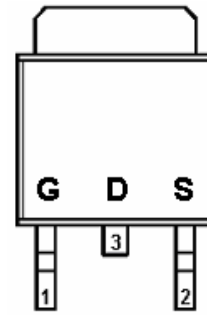
- ◆ 30V/20A, $R_{DS(ON)} = 12m\Omega @ V_{GS} = 10V$
- ◆ 30V/15A, $R_{DS(ON)} = 17m\Omega @ V_{GS} = 4.5V$
- ◆ Super high density cell design for extremely low $R_{DS(ON)}$
- ◆ Exceptional on-resistance and maximum DC current capability
- ◆ TO-252 package design

APPLICATIONS

- Power Management in Note book
- Powered System
- DC/DC Converter
- Load Switch

PIN CONFIGURATION

TO-252



PART MARKING





SPN8878

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PIN DESCRIPTION

Pin	Symbol	Description
1	G	Gate
2	S	Source
3	D	Drain

ORDERING INFORMATION

Part Number	Package	Part Marking
SPN8878T252RGB	TO-252	SPN8878

※ SPN8878T252RG : Tape Reel ; Pb – Free ; Halogen - Free

ABSOLUTE MAXIMUM RATINGS

(TA=25°C Unless otherwise noted)

Parameter	Symbol	Typical	Unit	
Drain-Source Voltage	V _{DSS}	30	V	
Gate –Source Voltage	V _{GSS}	±20	V	
Continuous Drain Current	I _D	TA=25°C	18	A
		TA=100°C	13	
Pulsed Drain Current	I _{DM}	40	A	
Continuous Drain Current	I _S	5	A	
Power Dissipation	P _D	TA=25°C TO-252-2L	40	W
		TO-251	55	
Operating Junction Temperature	T _J	150	°C	
Storage Temperature Range	T _{STG}	-55/150	°C	
Thermal Resistance-Junction to Ambient	R _{θJA}	100	°C/W	



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ELECTRICAL CHARACTERISTICS

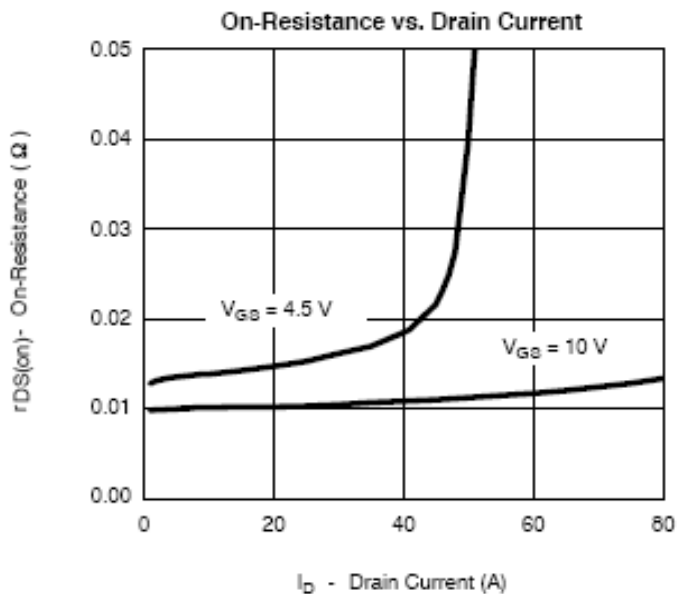
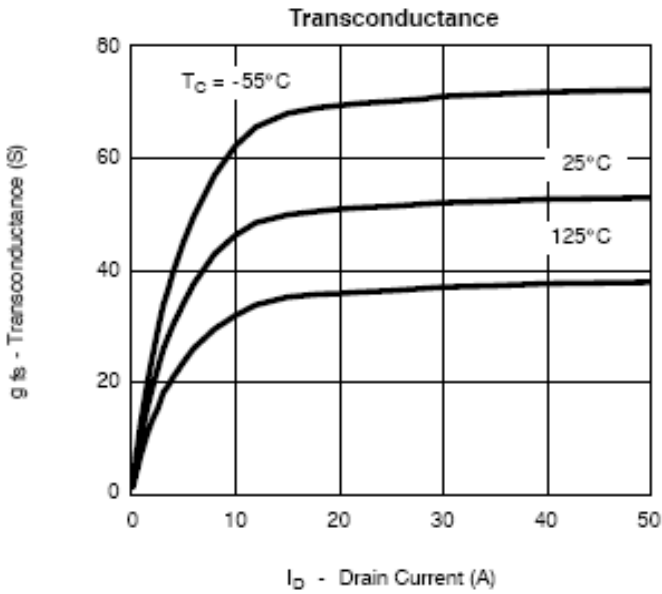
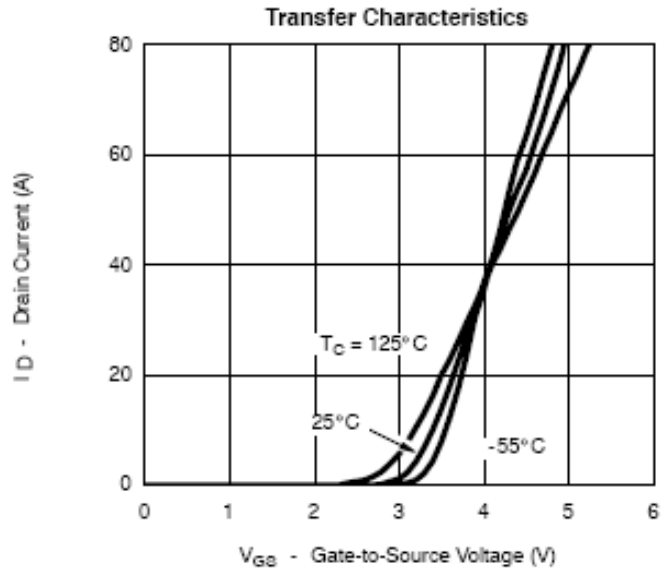
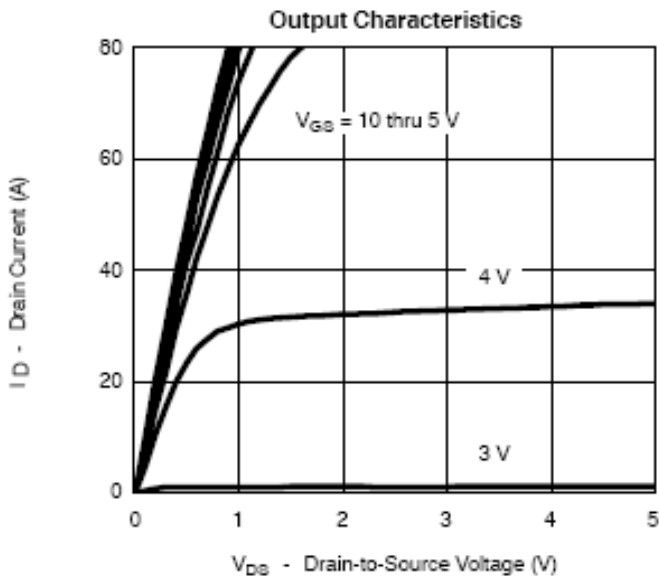
(T_A=25°C Unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V, I _D =250μA	30			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1.0		3.0	
Gate Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±20V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =24V, V _{GS} =0V			1	μA
		V _{DS} =24V, V _{GS} =0V T _J =85°C			5	
On-State Drain Current	I _{D(on)}	V _{DS} ≥5V, V _{GS} =10V	40			A
Drain-Source On-Resistance	R _{DSON}	V _{GS} =10V, I _D =20A		0.010	0.012	Ω
		V _{GS} =4.5V, I _D =15A		0.013	0.017	
Forward Transconductance	g _{fs}	V _{DS} =15V, I _D =20A	15			S
Diode Forward Voltage	V _{SD}	I _S =40A, V _{GS} =0V		0.8	1.5	V
Dynamic						
Total Gate Charge	Q _g	V _{DS} =15V, V _{GS} =10V I _D =50A		28	42	nC
Gate-Source Charge	Q _{gs}			6		
Gate-Drain Charge	Q _{gd}			5		
Input Capacitance	C _{iss}	V _{DS} =15V, V _{GS} =0V f=1MHz		1600		pF
Output Capacitance	C _{oss}			285		
Reverse Transfer Capacitance	C _{rss}			140		
Turn-On Time	t _{d(on)}	V _{DD} =15V, R _L =0.3Ω I _D =50A, V _{GEN} =10V R _G =1Ω		9	15	nS
	t _r			15	25	
Turn-Off Time	t _{d(off)}			20	30	
	t _f			12	20	



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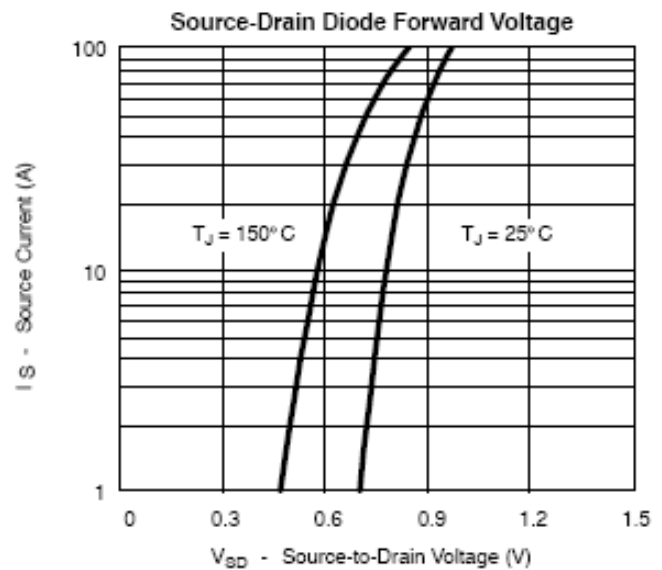
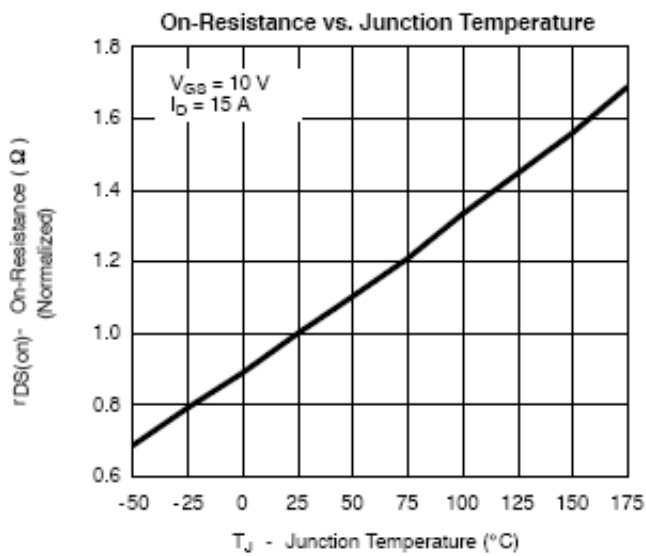
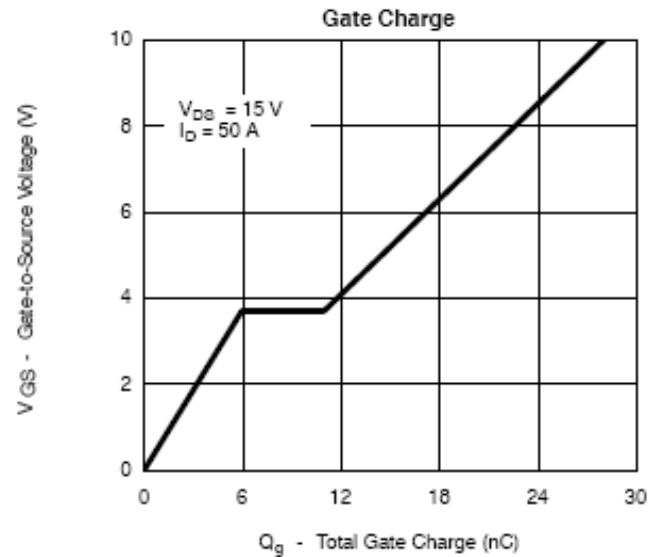
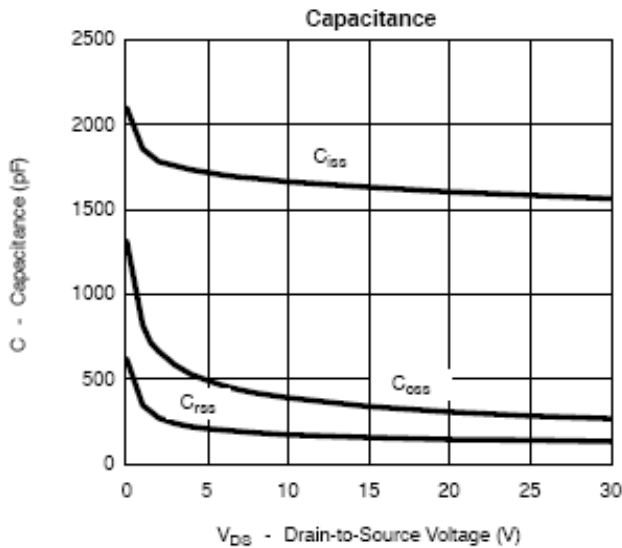
TYPICAL CHARACTERISTICS





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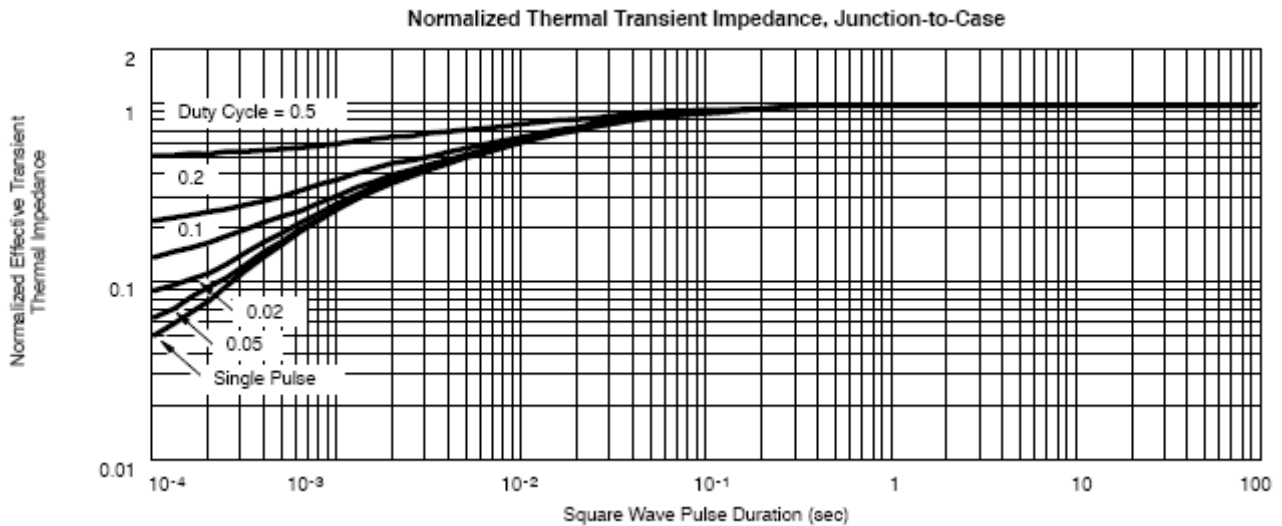
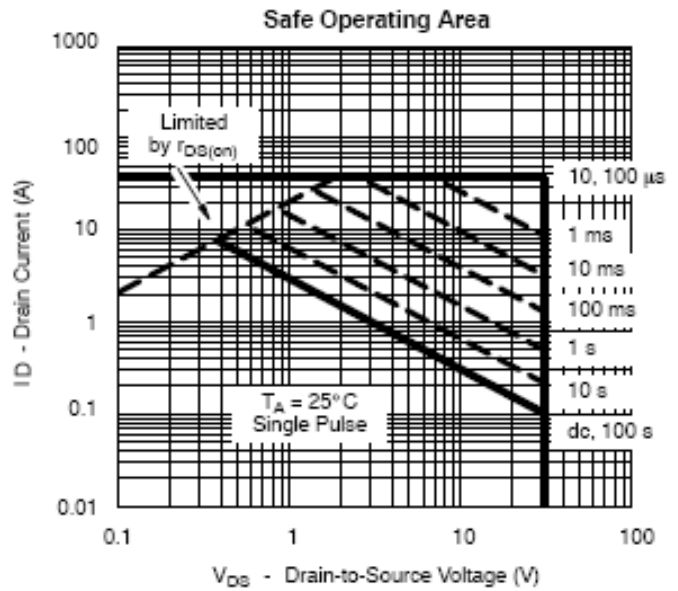
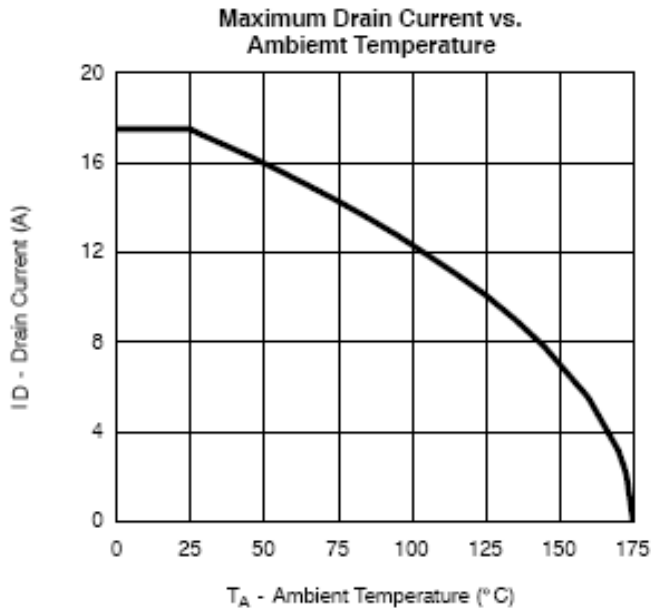
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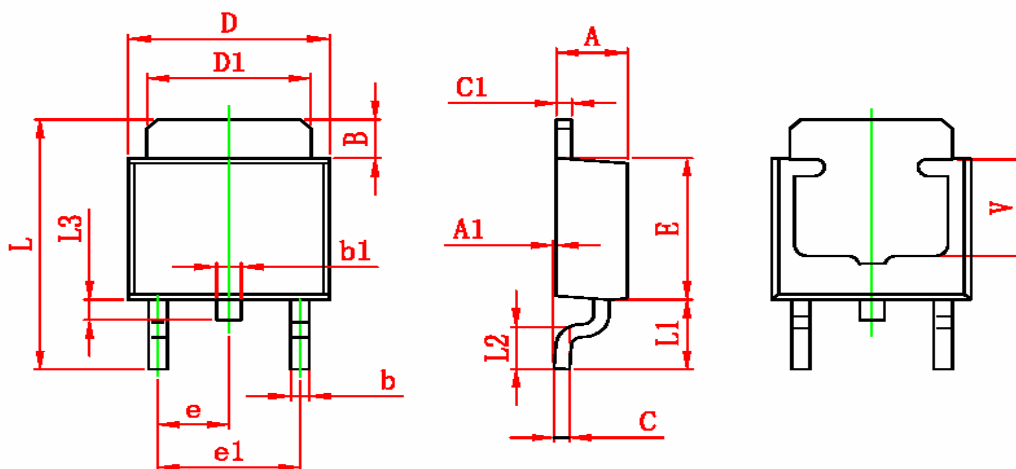
TYPICAL CHARACTERISTICS





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TO-252 PACKAGE OUTLINE



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
B	1.350	1.650	0.053	0.065
b	0.500	0.700	0.020	0.028
b1	0.700	0.900	0.028	0.035
c	0.430	0.580	0.017	0.023
c1	0.430	0.580	0.017	0.023
D	6.350	6.650	0.250	0.262
D1	5.200	5.400	0.205	0.213
E	5.400	5.700	0.213	0.224
e	2.300 TYP		0.091 TYP	
e1	4.500	4.700	0.177	0.185
L	9.500	9.900	0.374	0.390
L1	2.550	2.900	0.100	0.114
L2	1.400	1.780	0.055	0.070
L3	0.350	0.650	0.014	0.026
V	3.80 REF		0.150 REF	



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